



C-BAND POWER GaAs MESFET (2 WATTS)

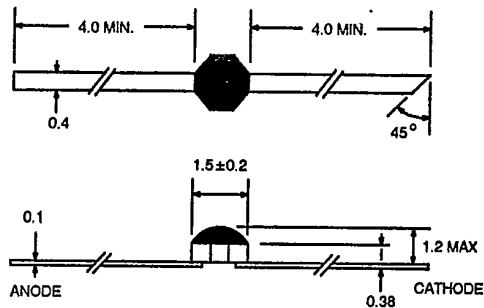
NE8004 SERIES

FEATURES

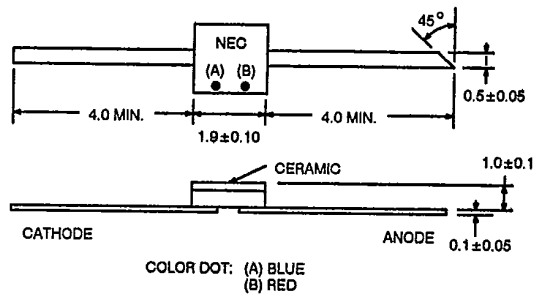
- HIGH SENSITIVITY
- LOW DRIVE LEVEL
- SMALL SIZE
- LOW COST

PHYSICAL DIMENSIONS (Units in mm)

3A PACKAGE*



3D PACKAGE



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _R	Reverse Voltage	V	4.0
V _{RM}	Peak Reverse Voltage	V	4.2
I _F	Forward Current	mA	30
I _{FM}	Peak Forward Current	mA	90
I _O	Average Rectified Current	mA	30
T _{STG}	Storage Temperature	°C	-65 to +150
T _J	Junction Temperature	°C	+150
T _{SDR}	Soldering Temperature	°C	+230*

*One time within 10 seconds.

*Moisture resistance of 3A package diode is about 500 Hr HHT (85°C, 85%), because 3A package has small mold potting structure. If you need hermetic package diode, 3D package is suitable.

ELECTRICAL CHARACTERISTICS (TA = 25°C)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	PART NUMBER PACKAGE CODE			PART NUMBER PACKAGE CODE		
			ND4131-3A 3A	ND4131-3D 3D	ND4131-3A 3A	ND4131-3D 3D		
V _R	Reverse Voltage At I _R = 10 μA	V	4.0			4.0		
V _F	Forward Voltage at I _F = 30 mA	V			1.0			1.0
C _T	Terminal Capacitance at f = 1 MHz, V _R = 0 V	pF			0.35			0.32
NF	Noise Figure at f = 9375 MHz, P _{IN} = 1 mW, N _{IF} = 1.5 dB	dB		6.5			6.5	



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TYPICAL PERFORMANCE CHARACTERISTICS (TA = 25°C)

